Structural and magnetic properties of DNTT, PTCDI-C8/LaSrMnO₃ bilayer



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Organic semiconductor is interested in connecting to spin-dependent electronics owing to their long spin relaxation time ⁽¹⁾ and low spin-orbit interaction. ⁽²⁾ The organics itself can not be used as a spin source at room temperature (RT); therefore, the organic semiconductor needs to be in contact with magnetic materials. In this bilayer system, low damping magnetic materials and low mixing conductance at the interface are required. The LaSrMnO₃ (LSMO) epitaxial films exhibited very low damping constant in the in-plane direction at RT. ⁽³⁾ The oxide materials are surface stable in the atmospheric condition compared with metals; which can be an efficient spin source for organic semiconductors. In this study, the organic semiconductor materials of DNTT and PTCDI-C8 (t = 5 nm) was deposited on the LSMO epitaxial films (t = 70 nm) and systematically investigated structure and magnetic properties. Figure 1 show the XAS and XMCD spectrum. Superposition of Mn- L_3 was normalized isotropic XAS spectra. In the case of LSMO/PTCDI-C8 bilayer of XAS spectra, the Mn⁴⁺ at the interface was increased when deposited at 180°C which probably due to the electron-acceptor nature of PTCDI -C8. ^(4, 5) The PTCDI-C8 at 180°C showed decreases of Mn moments which is corresponding to decrease of Mn³⁺. Thus, RT deposition for PTCDI-C8 and DNTT can expect for efficient spin injection or spin-dependent transport. We also present magnetic properties by M - H loops and structural analyses using synchrotron X-ray diffraction.



Figure 1 XAS and XMCD spectrum for LaSrMnO₃ and DNTT, PTCDI / LaSrMnO₃ bilayer.

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